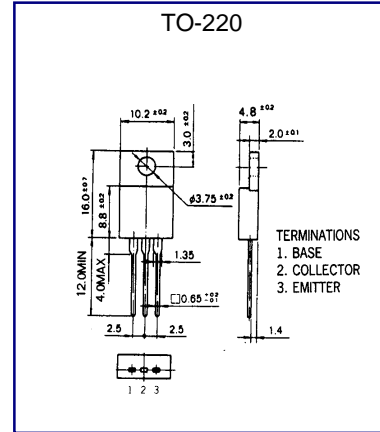




BU406/406H/408

NPN EPITAXIAL SILICON TRANSISTOR

**HIGH VOLTAGE SWITCHING USE IN
HORIZONTAL DEFLECTION OUTPUT STAGE**



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

| Characteristic | Symbol | Rating | Unit |
|--|------------------|---------|------|
| Collector-Base Voltage | V _{CB0} | 400 | V |
| Collector-Emitter Voltage | V _{CE0} | 200 | V |
| Emitter-Base voltage | V _{EB0} | 6 | V |
| Collector Current (DC) | I _C | 7 | A |
| Collector Peck Current | I _{CM} | 10 | A |
| Base Current (DC) | I _B | 4 | A |
| Collector Dissipation (T _c =25°C) | P _C | 60 | W |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature | T _{stg} | -65~150 | °C |

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|--|----------------------|---|-----|-----|------|------|
| Collector Cutoff Current (V _{BE} =0) | I _{CES} | V _{CE} = 400V , V _{EB} = 0 | | | 5 | mA |
| | | V _{CE} = 250V , V _{EB} = 0 | | | 100 | μA |
| | | V _{CE} = 250V , V _{EB} = 0 | | | 1 | mA |
| Emitter Cutoff Current(I _C =0) | I _{EBO} | V _{CE} = 250V , V _{EB} = 0 | | | 1 | mA |
| Collector Emitter Saturation Voltage :BU406 :BU406H :BU408 | V _{CE(sat)} | T _c =150 | | | 1 | V |
| | | V _{EB} = 6V , I _C =0 | | | 1 | V |
| | | I _C =5A, I _B =0.5A | | | 1.2 | V |
| | | I _C =5A, I _B =0.8A | | | 1.2 | V |
| Base- Emitter Saturation Voltage :BU406 :BU406H :BU408 | V _{BE(sat)} | I _C =6A, I _B =1.2A | | | 1.5 | V |
| | | I _C =5A, I _B =0.5A | 10 | | | MHZ |
| | | I _C =5A, I _B =0.8A | | | 0.75 | μS |
| Current Gain Bandwidth Product | f _T | I _C =5A, I _B =0.8A | | | 0.4 | μS |
| | | I _C =6A, I _B =1.2A | | | 0.4 | μS |
| | | V _{CE} = 10V , I _C =500mA | | | | |
| | | I _C =5A, I _B =0.5A | | | | |
| Turn-Off Time :BU406 :BU406H :BU408 | t _{off} | I _C =5A, I _B =0.8A | | | | |
| | | I _C =6A, I _B =1.2A | | | | |
| | | I _C =5A, I _B =0.8A | | | | |